

800V N-Channel MOSFET

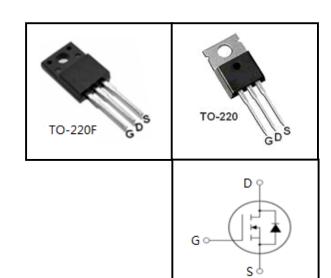
FEATURES

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

APPLICATIONS

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)

Device Marking and Package Information				
Device	Package	Marking		
CS9N80F	TO-220F	CS9N80F		
CS9N80P	TO-220	CS9N80P		



Absolute Maximum Ratings T _C = 25°C, unless otherwise noted					
Parameter	Symbol –	Va	l lmit		
Parameter		TO-220F	TO-220	Unit	
Drain-Source Voltage (V _{GS} = 0V)	V _{DSS}	800		V	
Continuous Drain Current	I _D	9		А	
Pulsed Drain Current (note1)	I _{DM}	36		А	
Gate-Source Voltage	V _{GSS}	±30		V	
Single Pulse Avalanche Energy (note2)	E _{AS}	405		mJ	
Avalanche Current (note1)	I _{AS}	9		Α	
Repetitive Avalanche Energy (note1)	E _{AR}	243		mJ	
Power Dissipation (T _C = 25°C)	P _D	25	70	W	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55~+150		°C	

Thermal Resistance					
Baramatar	Symbol	V	I Imit		
Parameter		TO-220F	TO-220	Unit	
Thermal Resistance, Junction-to-Case	R _{thJC}	5	1.78	12/\\\	
Thermal Resistance, Junction-to-Ambient	R _{thJA}	62.5	60	K/W	



Specifications $T_J = 25^{\circ}C$, unless otherwise noted								
Parameter	Symbol	T . O . IIV	Value					
		Test Conditions	Min.	Тур.	Max.	Unit		
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	800		1	V		
Zoro Coto Voltogo Drain Current	I _{DSS}	$V_{DS} = 800V, V_{GS} = 0V, T_{J} = 25^{\circ}C$	-		1	μΑ		
Zero Gate Voltage Drain Current		$V_{DS} = 640V, V_{GS} = 0V, T_{J} = 125^{\circ}C$	1		100			
Gate-Source Leakage	I _{GSS}	$V_{GS} = \pm 30V$			±100	nA		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		4.0	V		
Drain-Source On-Resistance (Note3)	R _{DS(on)}	$V_{GS} = 10V, I_D = 4.5A$		1	1.2	Ω		
Dynamic								
Input Capacitance	C _{iss}	$V_{GS} = 0V,$ $V_{DS} = 25V,$		1519		pF		
Output Capacitance	C _{oss}			162				
Reverse Transfer Capacitance	C_{rss}	f = 1.0MHz		34				
Total Gate Charge	Q_g	$V_{DD} = 640 \text{V}, I_{D} = 9 \text{A}, $ $V_{GS} = 10 \text{V}$		57		nC		
Gate-Source Charge	Q_{gs}			24				
Gate-Drain Charge	Q_{gd}			7.5				
Turn-on Delay Time	t _{d(on)}			45		ns		
Turn-on Rise Time	t _r	$V_{DD} = 400V, I_{D} = 9A,$		17				
Turn-off Delay Time	t _{d(off)}	$R_G = 25 \Omega$		355				
Turn-off Fall Time	t _f			475				
Drain-Source Body Diode Character	istics							
Continuous Body Diode Current	I _S	T 05.00			9	А		
Pulsed Diode Forward Current	I _{SM}	T _C = 25 °C			36			
Body Diode Voltage	V _{SD}	$T_J = 25^{\circ}\text{C}, I_{SD} = 4.5\text{A}, V_{GS} = 0\text{V}$			1.4	V		
Reverse Recovery Time	t _{rr}	$V_{GS} = 0V, I_{S} = 9A,$		562		ns		
Reverse Recovery Charge	Q _{rr}	di _F /dt =100A /μs		4.399		μC		

Notes

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L=10mH, V_{DD} = 50V, R_G = 25 Ω , Starting T_J = 25 $^{\circ}C$
- 3. Pulse Test: Pulse width ≤ 300µs, Duty Cycle ≤ 1%



Typical Characteristics $T_J = 25^{\circ}C$, unless otherwise noted

Figure 1. Output Characteristics (T_J = 25°C)

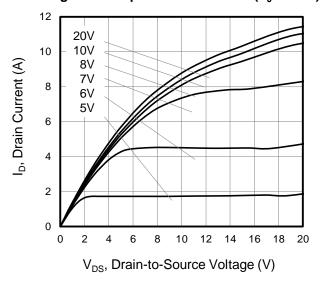


Figure 2. Body Diode Forward Voltage

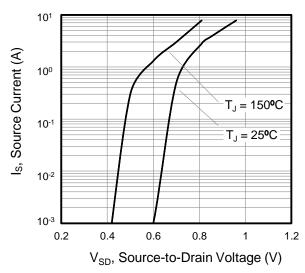


Figure 3. Drain Current vs. Temperature

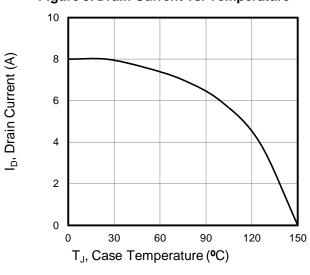


Figure 4. BV_{DSS} Variation vs. Temperature

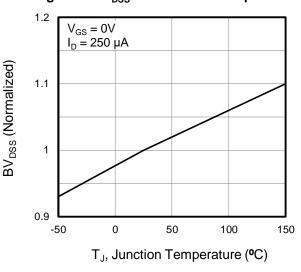


Figure 5. Transfer Characteristics

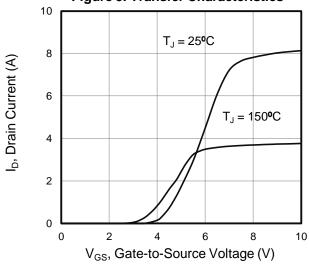
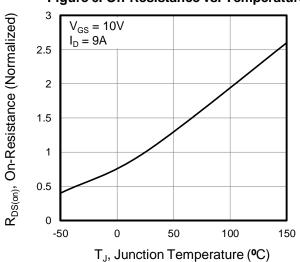


Figure 6. On-Resistance vs. Temperature





Typical Characteristics $T_J = 25^{\circ}\text{C}$, unless otherwise noted

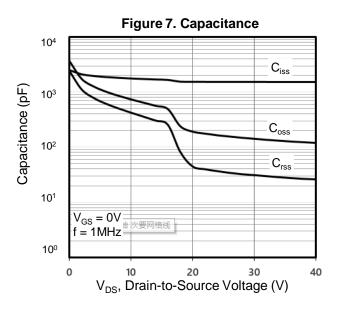


Figure 9. Transient Thermal Impedance

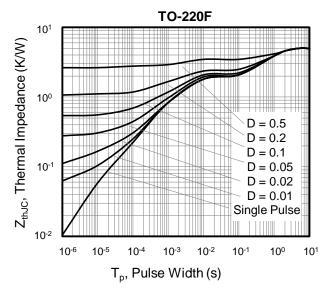


Figure 8. Gate Charge

V_{DD} = 160V
V_{DD} = 400V
V_{DD} = 640V
V_{DD} = 640V
Q_q, Total Gate Charge (nC)

Figure 10. Transient Thermal Impedance

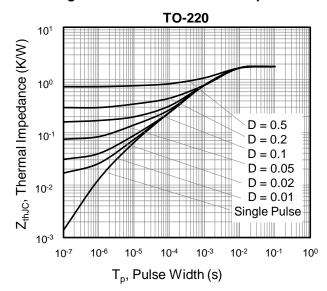




Figure A: Gate Charge Test Circuit and Waveform

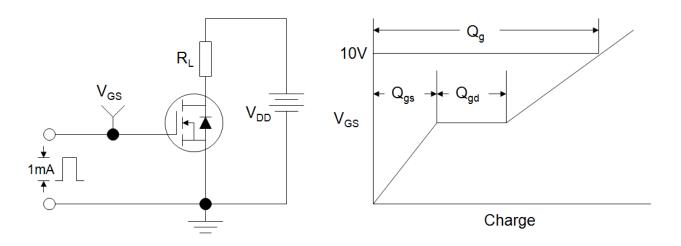


Figure B: Resistive Switching Test Circuit and Waveform

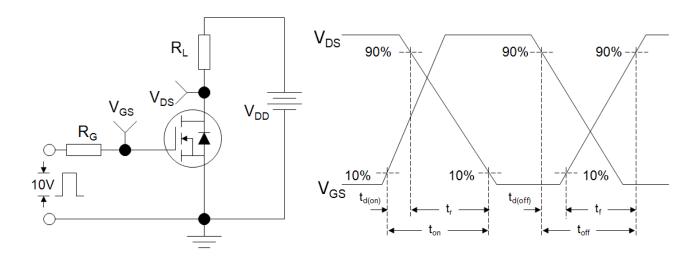
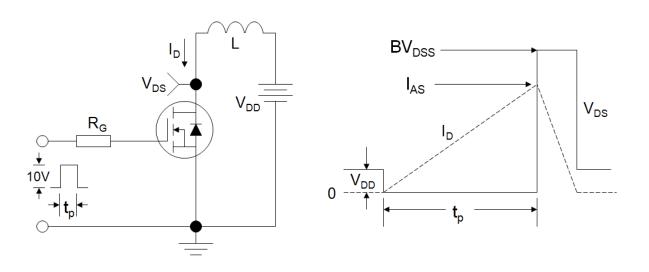
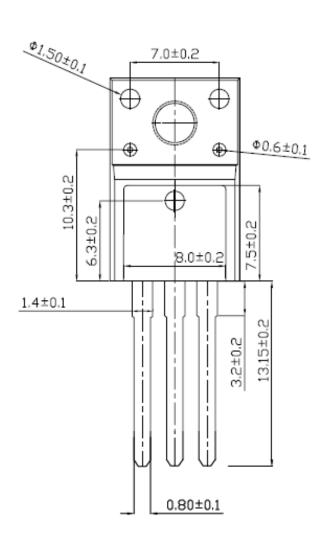


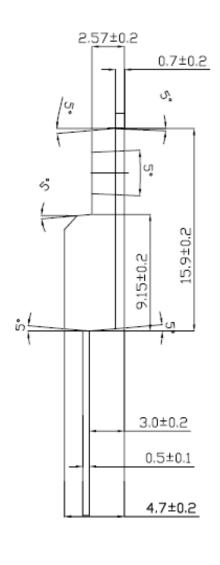
Figure C: Unclamped Inductive Switching Test Circuit and Waveform





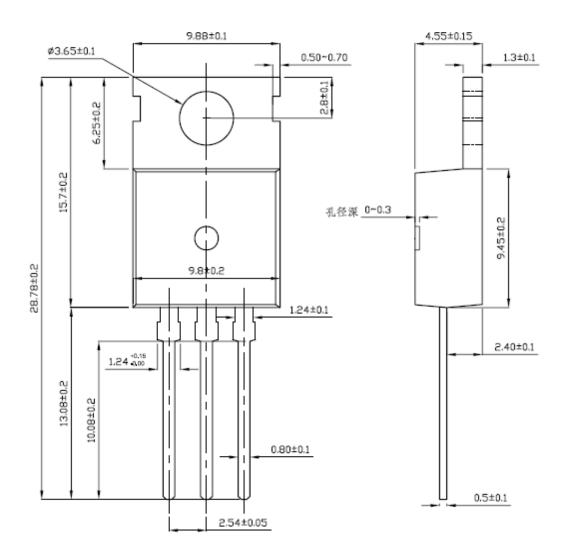
TO-220F







TO-220





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